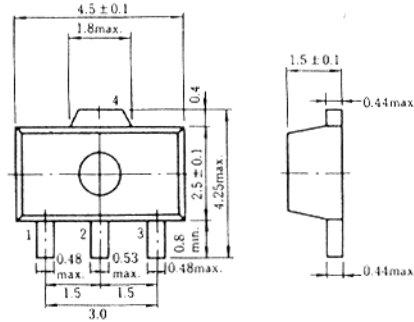


2SB1026

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER

Complementary pair with 2SD1419



(UPAK)

1. Base
 2. Collector
 3. Emitter
 4. Collector (Flange)
- (Dimensions in mm)

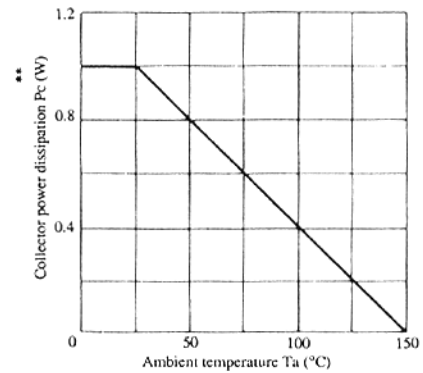
■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1026	Unit
Collector to base voltage	V _{CB0}	-120	V
Collector to emitter voltage	V _{CE0}	-100	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-1	A
Collector peak current	i _{C(peak)*}	-2	A
Collector power dissipation	P _{C**}	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10ms, Duty cycle ≤ 20%

** Value on the alumina ceramic board (12.5 × 20 × 0.7mm).

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-120	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-100	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -100V, I _E = 0	—	—	-10	μA
DC current transfer ratio	h _{FE1} *	V _{CE} = -5V, I _C = -150mA	60	—	200	
	h _{FE2}	V _{CE} = -5V, I _C = -500mA (Pulse test)	30	—	—	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -500mA, I _B = -50mA, (Pulse test)	—	—	-1	V
Base to emitter voltage	V _{BE}	V _{CE} = -5V, I _C = -150mA	—	—	-0.9	V
Gain bandwidth product	f _T	V _{CE} = -5V, I _C = -150mA	—	140	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	20	—	pF

* The 2SB1026 is grouped by h_{FE1} as follows.

Mark	DL	DM
h _{FE1}	60 to 120	100 to 200

■ See characteristic curves of 2SB1025.